

IN THE CLAIMS:

B

1. (Currently Amended): A semiconductor device comprising:
a capacitor formed above a semiconductor substrate and including
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,
a capacitor dielectric film formed on the storage electrode, and
a plate electrode formed on the capacitor dielectric film,
~~an upper cylinder edge of the storage electrode~~ the edge of the cylindrical projection being rounded and having a larger thickness than a thickness in ~~the a~~ rest portion. 1/ 2

2. (Currently Amended): A semiconductor device according to claim 1, wherein
the cylindrical-shaped storage electrode has a thickness gradually thickened toward ~~to the upper cylinder edge~~ the edge of the cylindrical projection.

3. (Currently Amended): A semiconductor device according to claim 1, wherein
a side surface of the storage electrode cylindrical projection is tilted and a ~~peripheral~~ circumferential length of ~~a cylinder~~ the cylindrical projection is gradually increased toward ~~to the upper cylinder edge~~ the edge of the cylindrical projection.

4. (Currently Amended): A semiconductor device according to claim 2, wherein
a side surface of the ~~storage electrode~~ cylindrical projection is tilted and a ~~peripheral~~ circumferential
length of ~~a cylinder~~ the cylindrical projection is gradually increased toward ~~to the upper cylinder edge~~ the
edge of the cylindrical projection.

B'
5-6. (Canceled)

7. (Currently Amended): A semiconductor device according to claim 1, wherein
~~an inner surface of the storage electrode~~ at a border portion between a side surface and a bottom
surface of the cylindrical-shaped storage electrode is rounded.

8. (Currently Amended): A semiconductor device according to claim 2, wherein
~~an inner surface of the storage electrode~~ at a border portion between a side surface and a bottom
surface of the cylindrical-shaped storage electrode is rounded.

9. (Currently Amended): A semiconductor device comprising:
a capacitor formed above a semiconductor substrate and including
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the
cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,

a capacitor dielectric film formed on the storage electrode, and
a plate electrode formed on the capacitor dielectric film,
the cylindrical-shaped storage electrode being formed of a metal film and having a larger
thickness at ~~an upper cylinder edge~~ the edge of the cylindrical projection than a thickness in a rest portion.

what's that?

10. (Currently Amended): A semiconductor device according to claim 9, wherein
the cylindrical-shaped storage electrode has a thickness gradually thickened toward ~~to the upper~~
~~cylinder edge~~ the edge of the cylindrical projection.

11. (Currently Amended): A semiconductor device comprising:
a capacitor formed above a semiconductor substrate and including
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the
cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,
a capacitor dielectric film formed on the storage electrode, and
a plate electrode formed on the capacitor dielectric film,
the cylindrical-shaped storage electrode being formed of a metal film and ~~an upper cylinder~~
~~edge of the storage electrode~~ the edge of the cylindrical projection being rounded.

12. (Currently Amended): A semiconductor device according to claim 11, wherein

the cylindrical-shaped storage electrode has a thickness gradually thickened toward to the upper

β' ~~cylinder edge~~ the edge of the cylindrical projection.

13-20. (Withdrawn)
